

## Features

- Low Reverse Leakage
- Low Forward Voltage Drop
- Guard Ring for Overvoltage Protection
- Isolated Hermetically Sealed Power Package
- Ceramic Seals for Improved Hermeticity
- Custom Lead Forming Available
- Eutectic Die Attach
- 150°C Operating Temperature
- Space Level Screening Available
- Available in TO-254Z Packaging

## Maximum Ratings (per diode)

Peak Repetitive Reverse voltage	$V_{RWM}$	45 V
Working Peak Reverse Voltage	$V_{RRM}$	45 V
DC Blocking Voltage	$V_R$	45 V
Average Forward Current, 25°C	$I_o$	15 A Note 1
Peak Surge Forward Current @ tp = 8.3 ms, half sinewave, $I_o = 0$ ; $V_{RM} = 0$	$I_{FSM}$	300 Apk
Peak Reverse Surge Current @ tp = 30µs, $V_{RSM} = 54$ V min, L = 260 µH	$I_{RRM}$	2 A
Thermal Resistance, Junction to Case	$R_{\theta jc}$	1.65 °C/W
Thermal Resistance, Junction to Ambient	$R_{\theta ja}$	40°C/W
Operating Junction Temperature	$T_j$	-65°C to 150°C
Storage Temperature	$T_{stg}$	-65°C to 150°C

## Electrical Characteristics per diode @ 25°C Unless Otherwise Specified

Parameter	Symbol	Typical	MA	Test Conditions
Maximum Instantaneous Forward Voltage	$V_F$	50 µA	0.55V	$I_F = 5$ A; $T_J = 25^\circ\text{C}^*$
			0.75V	$I_F = 15$ A; $T_J = 25^\circ\text{C}^*$
			1.0V	$I_F = 30$ A; $T_J = 25^\circ\text{C}^*$
			0.80V	$I_F = 15$ A; $T_J = -55^\circ\text{C}^*$
Maximum DC Reverse Current At Rated DC Blocking Voltage	$I_R$	50 µA	1 mA 40 mA	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
Junction Capacitance	$C_j$		2000 pF	$V_R = 5$ V, $f = 1$ MHz

\*Pulse test: Pulse width 300 µsec, Duty cycle 2%

Note:

1. Derate linearly @ 300mA/°C from  $T_J = T_C = +100^\circ\text{C}$  to 150°C

**1N6660**  
**1N6660R**  
MIL -S-19500/608

**30 Amp / 45 VOLTS**  
**COMMON CATHODE**  
**OR**  
**COMMON ANODE**  
**SCHOTTKY RECTIFIER**

